

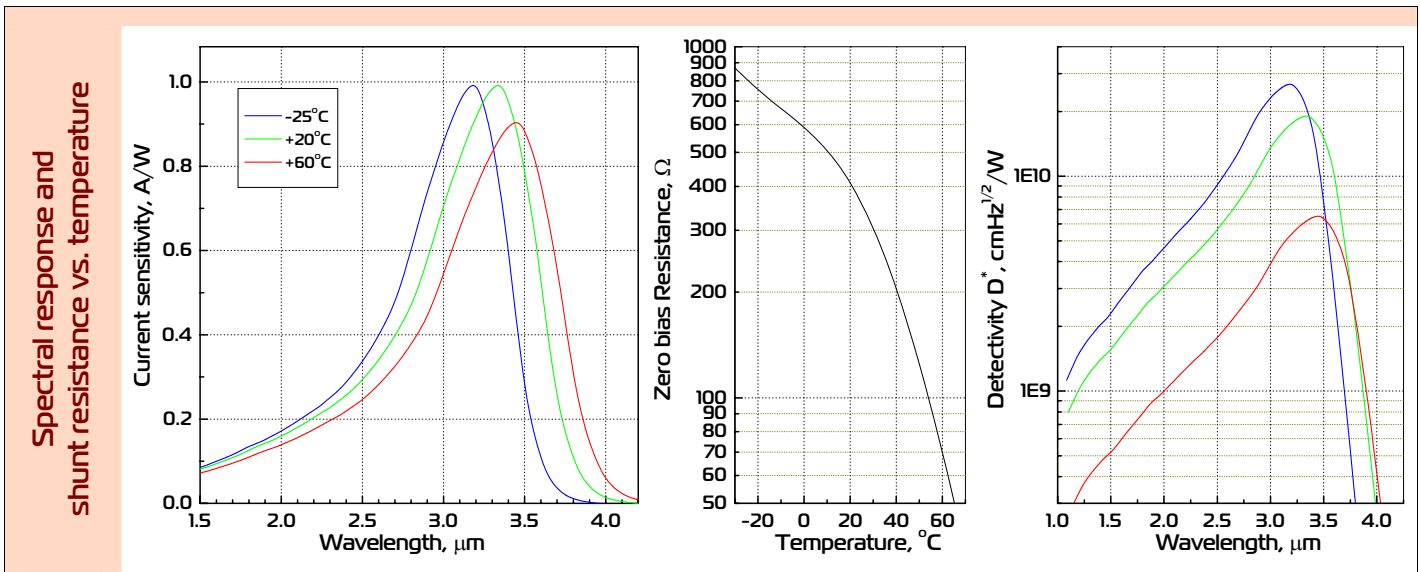
# InAs photodiode

# PD33fs mIL

Peak wavelength	$\lambda$	$\mu\text{m}$	$3.35 \pm 0.05$
Spectral response range	$\lambda_{0.1}$	$\mu\text{m}$	$1.75 \div 3.8$
Current sensitivity	$S_l$	$\text{A/W}$	$0.8 \div 1.0$
Resistance at zero bias	$R_o$	$\text{Ohm}$	$\geq 400$
Detectivity	$D^*_{\lambda_{\text{max}}}$	$\text{cmHz}^{1/2}/\text{W}^{-1}$	$\geq 1.5 \times 10^{10}$
Voltage sensitivity	$S_u$	$\text{V/W}$	$\geq 400$
Switching time	$\tau$	$\text{ns}$	$< 20$

Model	Package	Lens material; Cap with window	Sensitive area, mm	Angle of view FWHM, deg.	Operation conditions, °C	Polarity
PD33fs mILTO18	TO18	Chalcogenide glass	$\varnothing 1.0$	$\geq 60$	$-25 \div +60$	Leg near key is negative
PD33fs mILTO18c	TO18	Chalcogenide glass; Sapphire		50		

	PD33fs mILTO18	PD33fs mILTO18c
<b>Product view</b>		
<b>Features</b>	<p>Growth of narrow gap semiconductor alloys onto n<sup>+</sup>-InAs substrate; "Wide gap" window; Optical coupling through the use of chalcogenide glass lenses</p> <p>Data are valid for 22°C. Photodiode could be equipped with preamplifier that is designed for conversion of PD photocurrent into a convenient output voltage and is adjusted for the particular PD taking into account the R<sub>o</sub> value and frequency range. Other packages are available upon request</p>	<p>Ambient and high temperature operation; No bias required; Short time constant; High value of shunt resistance; Operation from DC to VHF; Highest long term stability</p>



Product specifications are subject to change without prior notice due to improvements or other reasons. Updated 26.11.12



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